

# RJK6014DPK

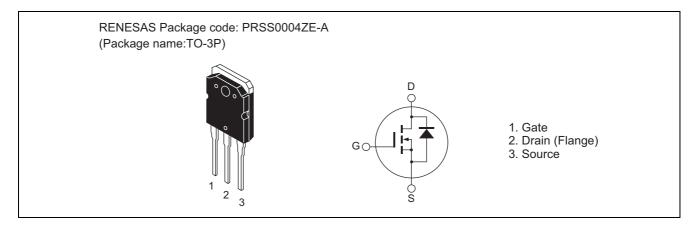
# Silicon N Channel MOS FET High Speed Power Switching

REJ03G1517-0200 Rev.2.00 Jun 04, 2007

#### **Features**

- Low on-resistance
- Low leakage current
- High speed switching

### **Outline**



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	600	V
Gate to source voltage	V <sub>GSS</sub>	±30	V
Drain current	I <sub>D</sub>	16	А
Drain peak current	I <sub>D (pulse)</sub> Note1	32	А
Body-drain diode reverse drain current	I <sub>DR</sub>	16	Α
Body-drain diode reverse drain peak current	I <sub>DR (pulse)</sub> Note1	32	А
Avalanche current	I <sub>AP</sub> Note3	5	А
Avalanche energy	E <sub>AR</sub> Note3	1.3	mJ
Channel dissipation	Pch Note2	150	W
Channel to case thermal impedance	θch-c	0.833	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tc = 25°C
- 3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C

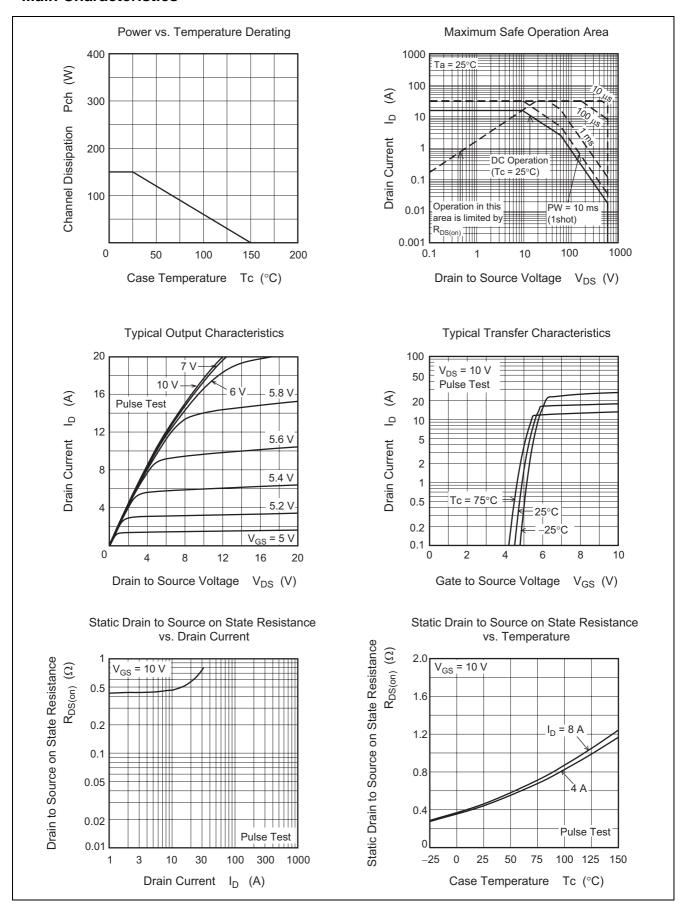
# **Electrical Characteristics**

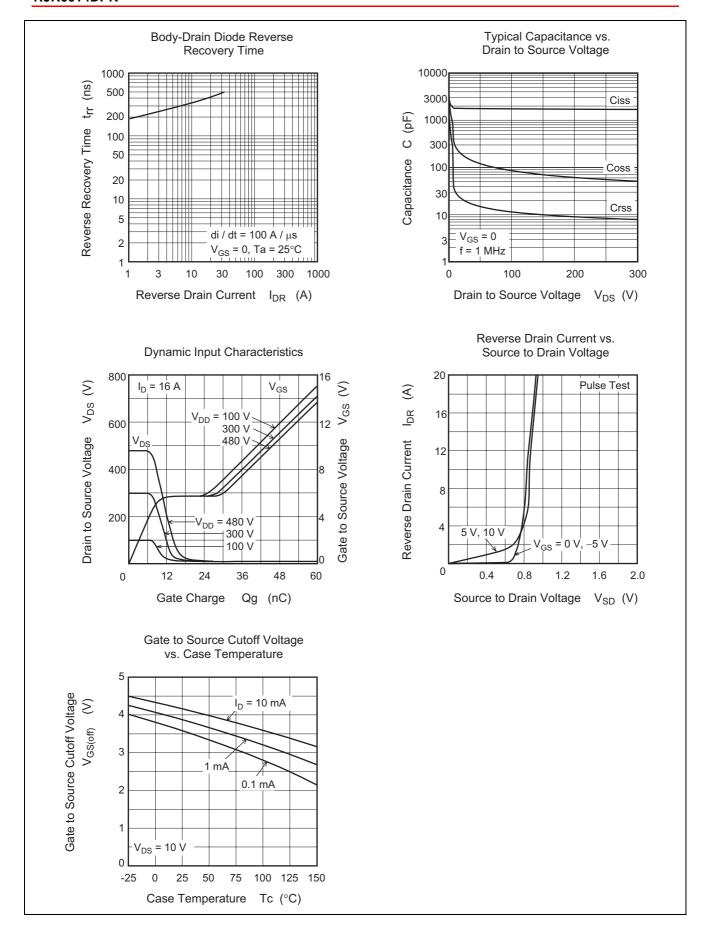
 $(Ta = 25^{\circ}C)$ 

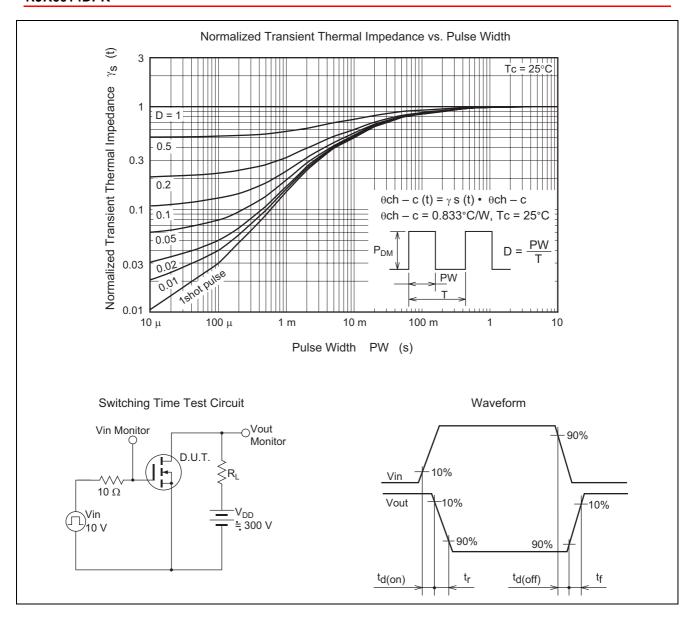
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600		_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>		_	1	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>	l	0.475	0.575	Ω	$I_D = 8 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss		1800	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	170	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	20	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d(on)</sub>	_	36	_	ns	I <sub>D</sub> = 8 A
Rise time	t <sub>r</sub>	_	29	_	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	$t_{d(off)}$	_	93	_	ns	$R_L = 37.5 \Omega$
Fall time	t <sub>f</sub>	_	20	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	45	_	nC	V <sub>DD</sub> = 480 V
Gate to source charge	Qgs	_	9	_	nC	V <sub>GS</sub> = 10 V
Gate to drain charge	Qgd	_	20	_	nC	I <sub>D</sub> = 16 A
Body-drain diode forward voltage	$V_{DF}$	_	0.91	1.50	V	$I_F = 16 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	390	_	ns	$I_F = 16 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 4. Pulse test

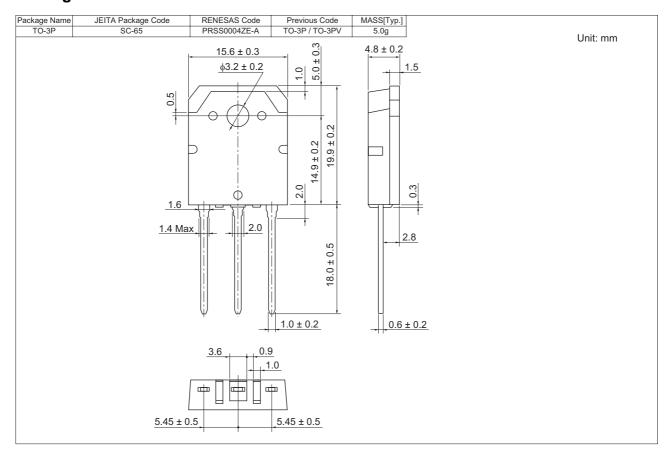
### **Main Characteristics**







# **Package Dimensions**



# **Ordering Information**

Part No.	Quantity	Shipping Container
RJK6014DPK-00-T0	360 pcs	Box (Tube)

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